

## Silicon NPN Power Transistors

2SC4242

## DESCRIPTION

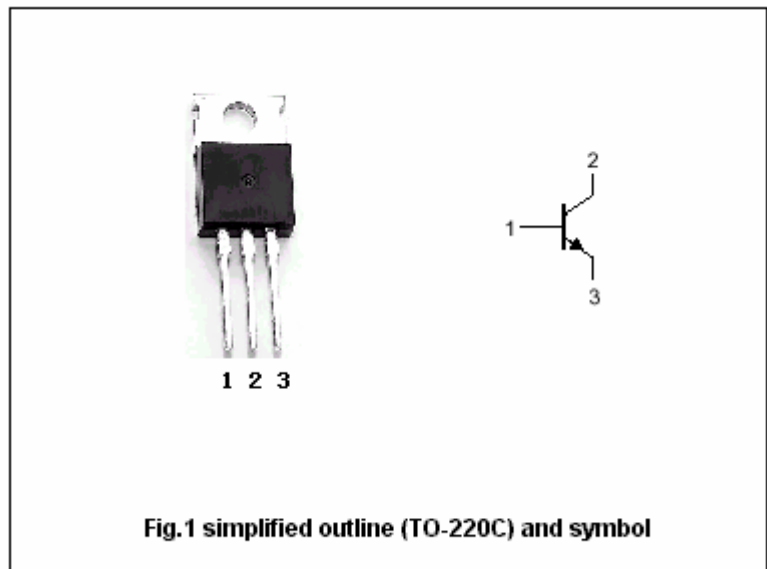
- With TO-220C package
- High voltage ,high speed

## APPLICATIONS

- For use in high voltage ,high speed; power switching in inductive circuit.
- Particularly suited for 115 and 220V switchmode applications such as switching regulators ,inverters ; DC-DC converters

## PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

Absolute maximum ratings( $T_a=25^\circ\text{C}$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	450	V
$V_{CEO}$	Collector-emitter voltage	Open base	400	V
$V_{EBO}$	Emitter-base voltage	Open collector	8	V
$I_C$	Collector current (DC)		7	A
$I_{CM}$	Collector current-Peak		14	A
$I_B$	Base current		2	A
$P_C$	Collector dissipation	$T_C=25^\circ\text{C}$	40	W
$T_j$	Junction temperature		150	$^\circ\text{C}$
$T_{stg}$	Storage temperature		-50~150	$^\circ\text{C}$

## THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
$R_{th\ j-c}$	Thermal resistance from junction to case	3.125	$^\circ\text{C}/\text{W}$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>CEO(SUS)</sub>	Collector-emitter sustaining voltage	I <sub>C</sub> =0.1A ; I <sub>B</sub> =0	400			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =1mA ; I <sub>E</sub> =0	450			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =1mA ; I <sub>C</sub> =0	8			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.8A			0.8	V
V <sub>BEsat</sub>	Base-emitter saturation voltage	I <sub>C</sub> =4A ; I <sub>B</sub> =0.8A			1.2	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =450V ; I <sub>E</sub> =0			100	μA
I <sub>EBO</sub>	Emitter cut-off current	V <sub>EB</sub> =8V ; I <sub>C</sub> =0			100	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =4A ; V <sub>CE</sub> =5V	10			
f <sub>T</sub>	Transition frequency	I <sub>C</sub> =0.4A ; V <sub>CE</sub> =10V		20		MHz
C <sub>ob</sub>	Collector output capacitance	f=1MHz ; V <sub>CB</sub> =10V		50		pF

## Switching times

t <sub>on</sub>	Turn-on time	I <sub>C</sub> =5A, I <sub>B1</sub> =1A I <sub>B2</sub> =-1A; V <sub>CC</sub> =150V R <sub>L</sub> =30Ω			1.0	μs
t <sub>s</sub>	Storage time				2.5	μs
t <sub>f</sub>	Fall time				0.5	μs

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PACKAGE OUTLINE

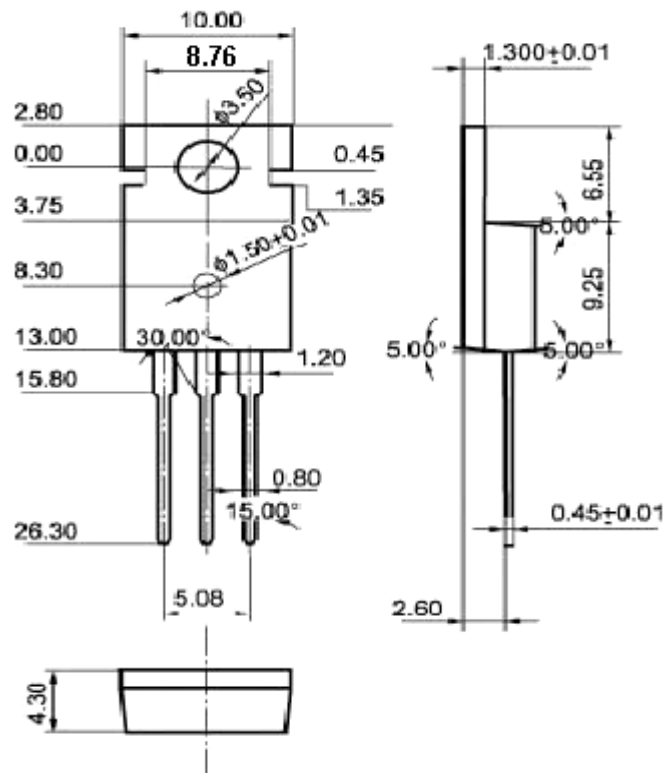


Fig.2 Outline dimensions (unindicated tolerance:  $\pm 0.10$  mm)

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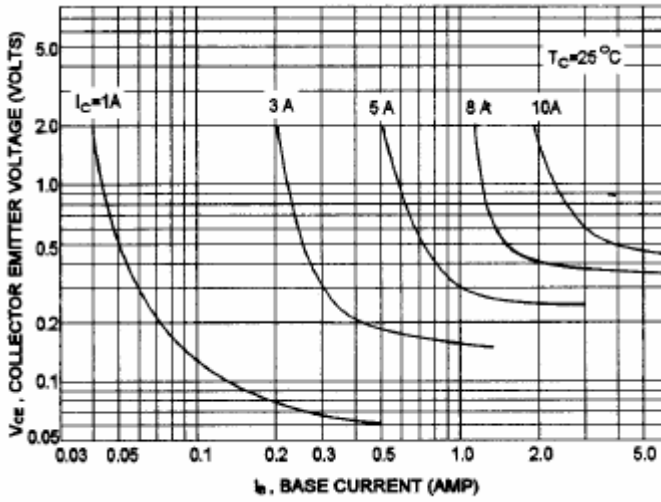


Fig.3 Static Characteristic

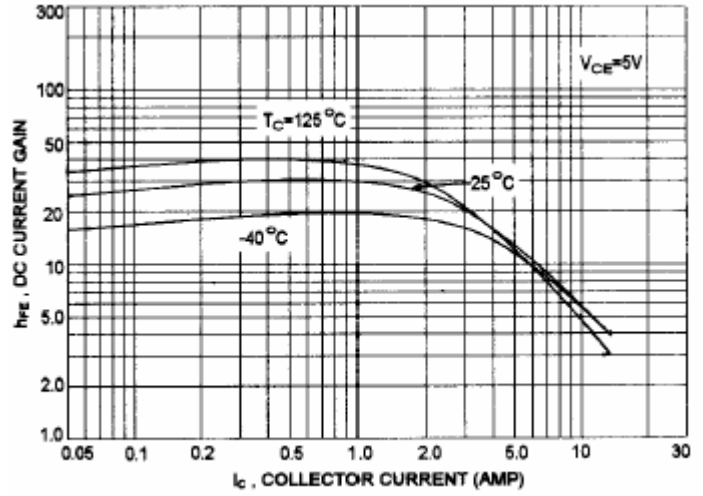


Fig.4 DC current Gain

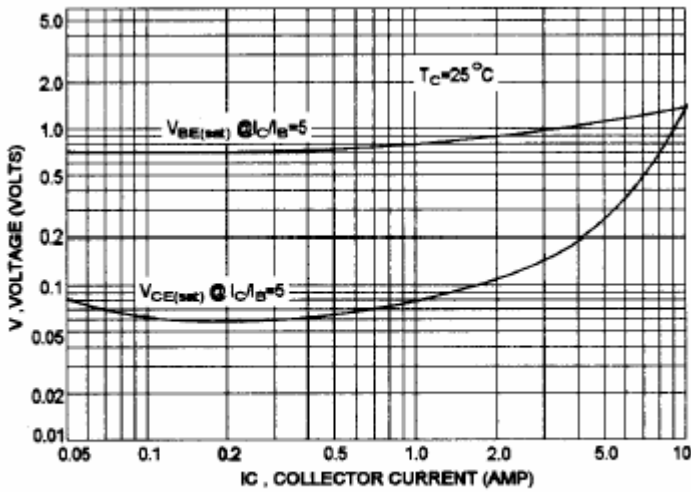


Fig.5 Base-Emitter Saturation Voltage  
Collector-Emitter Saturation Voltage

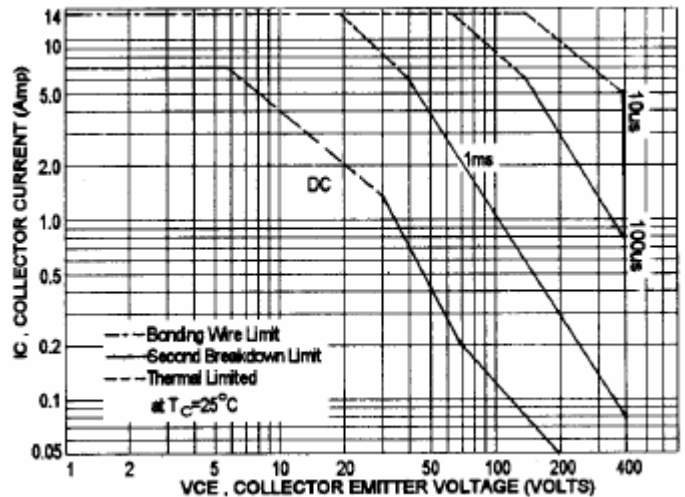


Fig.6 Safe Operating Area